CHECKLIST FOR SELECTING NEW EQUIPMENT OR NEW PROCESSES

Refer to specification 12100 for the definition of a new equipment and a new process.

Equipment:	IVS 130/135	
Process:	Overlay Metrology in Fab 2	
Responsible engineer:	Leo Schlegel/ Filip Rigole	
Date:	24-10-2003	
		value/OK/ attach
. Process requirement		
Technology and re	liability requirements	
List the physica	Il parameters (thickness, resistivity,) describing the process	
Defect density <u>requ</u>	uirements_	
Allowed machin	ne added defects/wfr	5 /# > 0.1 micron
Expected edge	of wafer effects, Si utilization	NA
Defect measure	ement method (KLA, Surfscan,)	Surfscan
2. Productivity		
Naked throughput		90 WPH
Set-up/conditioning	g method and time	
• Equipment monitor	ring method and time	
 Process monitoring 	g method and time	
3. Availability		
Mean Wafer Between	een Cleans (MWBC)	
 Mean Time Between 	en Failure (MTBF)	1500 hours
 Mean Time To Rep 	pair (MTTR)	4 hours
 Scheduled downting 	me	< 1 %
 Unscheduled dowr 	ntime	< 2 %
		A

CHECKLIST FOR SELECTING NEW EQUIPMENT OR NEW PROCESSES - Standard form for descriptive spec

DS12100

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Page 1 of 5

Location: NA

	Typical frequency	10.000 #
	Recovery procedure and time	0.5 hours
	• Power dip	
	Sensitivity	
	Recovery procedure	0.5 hours
	afety aspects ride this information to the safety manager!	
	List the safety considerations that have to be made:	
,	 Is the new tool CE compliant? If not, who will do the CE marking? 	Yes
	 Do you have a signed copy of the CE certificate of conformity? 	
1	Does the tool use ionising radiation?	No
	 Does the equipment or process use chemicals or gases ? If yes, what chemicals or gases ? 	No
	Is a recent MSDS or CPI card available of the chemicals or gases?	N
	Does the tool contain or process <u>liquid</u> chemicals? If you is the tool made out of non-combustible material?	No
	If yes, is the tool made out of non-combustible material? Specify material:	
	If not or if flammable liquids are processed, does the tool have an automatic	
	extinguishing system ?	
_		
	nvironmental aspects ide all this information to the environmental officer!	
	List all special environmental aspects that have to be considered:	
	Does the equipment or process have an impact on the water usage?	No
	Does the tool or process require DI-water? If yes, how much?	No
1	At the maximum capacity, what is the estimated quantity of waste water discharged?	
	List expected constituents in waste water	
	What's the expected pH of the waste water, acid or base?	
	Does the equipment or process require gases?	No
	What gases are needed?	
	At maximum capacity, what volume is needed of every gas in 1 yr?	
	Will the amount of stored gases change? If yes, how much will be added or removed?	
	Does the new tool or the tool where the new process is added have abatement (scrubber)?	
	 Does the equipment or process require liquid chemicals? 	No
A 41 4	Semiconductor Belgium BVBA	

CHECKLIST FOR SELECTING NEW EQUIPMENT OR NEW PROCESSES - Standard form for descriptive spec

DS12100

STF-0153, Revision: 4.0 Revision date: 02-JUL-03

Page 2 of 5 Location: NA What liquid chemicals are needed?

At maximum capacity, what volume is needed of every liquid chemical in 1 yr? At maximum capacity, estimate the quantity of each type of hazardous waste expected?

yr?

6. Fab Layout

Define the location of new equipment in Fab taking into account production, maintenance and facilities considerations

Litho Fab 2

7. Facility and bypack requirements

· List the required facilities:

Floorspace (measurement unit + operator console dimensions) Weight	124.5 cm x 94 cm + 62.5 cm x 83.8 cm 453.5 kg
Vibration requirements : 2 microns peak to peak below 7 Hz 0.5 microns peak to peak 7 Hz to 150 Hz 2.0 microns peak to peak above 150 Hz	Similar to stepper vibration system
Power requirements	115 V 50/60 Hz, 20 Amp, single phase
Heat dissipation	NA
Exhaust	NA
DI-water	NA
City water	NA
Cooling water	NA
Vacuum	-24 to -27 in HG, 0.8 cfm, hose fitting 1/4 in OD
Clean Compressed Air	90 psi 2cfm, hose fitting ¼ inch
Chemical distribution system	NA
Gases	NA
Detection (gas, fire, leak)	NA
Drain	NA
Waste treatment	NA

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CHECKLIST FOR SELECTING NEW EQUIPMENT OR NEW PROCESSES - Standard form for descriptive spec

DS12100

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Location: NA

List the required bypack equipment	
Vacuum pumps	NA
Heat exchangers	NA
Gas scrubbers/environmental requirements	NA
Transformers	
Λ	
3. Maintainability	
Spares: typical set (cost & lifetime) & common spares with existing equipmen	t 31 K \$
PM kits/swap kits: kit of parts required for a specific PM	
Documentation:	
Spare parts list	
Exploded mechanical drawings	
Schematics (electronics, gas distribution,)	
Maintenance manual procedures and frequency	
Support, possibility to have:	-
On-site support for set-up and maintenance	YES
Training at vendor site (process-operator / maintenance)	YES
Expert training from field experts on site	YES
	1
). Manufacturing integration	
Back-up scenarios from and to other equipment	YES
 Possibility of retrofitting other technologies 	YES
 Reclaim procedure for monitor and conditioning wafers 	NA
Link with CIM infrastructure	Extra cost
- automation/LIS/data communication	7
compatibility with other wafer sizes	4 to 8 inch
Ost Investments:	
Equipment (incl. options)	
Facilities	
Safety/environment (precautions/adaptations)	NA
Bypack	
Spare kits	31 k \$
• Expenses:	OIN
AMI Semiconductor Belgium BVBA	
CHECKLIST FOR SELECTING NEW EQUIPMENT OR NEW PROCESSES - Standard form for descr	riptive spec
S12100	•
STF-0153, Revision: 4.0 Page 4 of 5 Revision date: 02-JUL-03 Location: NA	
CONTROL MARCO DE DUE DU	

Consumables / raw materials per waferpass	NA
Cost of maintenance (PM + cleaning) (incl. bypack)	
Maintenance contract	NA
Monitoring and conditioning (wafers and consumables)	
Cost of facilities (incl. waste treatment)	

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CHECKLIST FOR SELECTING NEW EQUIPMENT OR NEW PROCESSES - Standard form for descriptive spec

DS12100

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Page 5 of 5

Location: NA



1750 Halford Avenue, Suite 218 Santa Clara, CA 95051

February 27, 2004

License Grant

AMI Semiconductor, Belgium

MetroBoost, a California Company, hereby grants to AMI Semiconductor, Belgium a permanent, non-revocable, non-transferable **package** license to use Overlay Booster software version 2.61.

Package license entitles AMI Semiconductor to install and use Overlay Booster on two computer systems in its Belgium facilities; one system for real-time operation with IVS overlay metrology tool serial number ACVR256 manufactured by Soluris, Inc. of Concord, MA, and a second computer system for off-line data analysis.

This license is non-transferable except in the event of the sale of IVS system serial number ACVR256 or its relocation to another AMI Semiconductor facility.

The license remains valid for any future software update or upgrade that MetroBoost would provide free of charge during the period of one year from the date of installation.

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Farid Askary President MetroBoost

Measurement System analysis Data Sheet Performed by : Soluris ivs Date: 25-Feb-04 Measurement System: HIMQN\180\OVERLAY Y direction Measurement Program: Operation number : 3537 LSL: -0.18 USL 0.18 В С operator Α T2 R T2 Т3 R Sample T1 T2 ТЗ R T1 Т3 T1 0.0105 0.0056 -0.0652 -0.0649 0.0006 -0.0686 -0.0581 -0.0671 -0.0625 -0.0638 -0.0681 -0.0646 1 0.0038 -0.028 0.0022 -0.0285 -0.0239 -0.02470.0046 2 -0.0287 -0.0249 -0.026-0.0264-0.0286 -0.0396 -0.0398 -0.0406 0.001 -0.0396 -0.0396 -0.0427 0.0031 -0.0408 -0.0374 -0.039 0.0034 3 -0.0178 -0.0192 -0.0157 0.0035 -0.0163 -0.0158 0.002 -0.0148 -0.0177 -0.0165 0.0029 4 -0.0159 -0.0367 -0.0398 -0.0362 0.0036 -0.0353 -0.0376 -0.0305 0.0071 -0.0345 -0.0341 -0.0344 0.0004 5 -0.0113 -0.0089 -0.0138 0.0049 -0.0138 -0.0117 0.0025 -0.0162 -0.0133 -0.0135 0.0029 6 -0.0127 -0.0223 -0.0222 -0.0249 0.0027 -0.0211 -0.0229 -0.0243 0.0032 -0.026 -0.0239 -0.0228 0.0032 7 8 -0.003 -0.0006 0.0005 0.0035 -0.0026 -0.0007 -0.0032 0.0025 -0.0014 -0.0031 0.0005 0.0036 0.0026 9 -0.0239 -0.0248 -0.02470.0009 -0.0253 -0.0231 -0.02490.0022 -0.0254 -0.0274-0.0248 0.0077 0.0104 0.0094 0.001 10 0.0097 0.0113 0.0108 0.0016 0.0115 0.0101 0.0038 0.0097 11 0 0 0 0 0 12 0 0 0 13 0 14 0 0 0 15 0 0 0 0.026 0.039 -0.235 -0.234 0.030 Totals -0.238 -0.234 -0.236 -0.241 -0.226 -0.240 -0.240 10 Ν 10 Ν Ν 10 Trials 3 2 Oper. T1 -0.238 T1 -0.241 T1 -0.240 T2 -0.226 T2 -0.235 T2 -0.234 -0.236 ТЗ -0.240 T3 -0.234 ТЗ SUM -0.707 SUM -0.708 SUM -0.709 -0.024 Xav -0.024 Xav -0.024 Xav Rav 0.003 Rav 0.004 Rav 0.003 Raverage 0.003 d_2 1.128 Xmax -0.024 UCLrange 0.010 D2s 1.910 -0.024 Xmin 0.000 3.267 0.000 D4 Xdelta 0.017 Repeatability: Variation in measurement when one operator uses the same instrument and measures the same parts

 Repeatability :
 0.017

 Reproducability :
 0.000

 R&R :
 0.017

 R&R % :
 4.70

Variation in measurement due to different operators or instruments, measuring the same parts

Total variation due to repeatability and reproducibility

Measurement System analysis Data Sheet IVS 25-Feb-04 Performed by : Soluris Date: Measurement System: HIMQN\180\OVERLAY X direction Measurement Program: Operation number : 3537 LSL -0.18 USL: 0.18 В c operator Α Sample R ТЗ R T2 T3 R T1 T2 T3 T1 T2 T1 0.0014 0.0228 0.0215 0.0197 0.0031 0.0224 0.0201 0.0234 0.0033 0.0216 0.0224 0.021 1 0.0527 0.056 0.0033 0.0536 0.0555 0.053 0.0025 0.0538 0.0556 0.0534 0.0022 2 0.0547 0.0292 0.0275 0.0296 0.0021 0.0284 0.0279 0.0298 0.0019 0.0284 0.0273 0.0283 0.0011 3 0.0555 0.0569 0.0571 0.0004 0.0547 0.0565 0.0563 0.0018 0.0562 0.0568 0.0013 4 0.0567 0.0394 0.0048 0.0409 0.0418 0.0411 0.0009 0.0429 0.0412 0.0396 0.0033 5 0.0442 0.0424 0.0027 0.0498 0.0029 0.052 0.0496 0.0502 0.0024 0.0525 0.0498 0.0524 6 0.0525 0.0496 0.0081 0.0005 0.007 0.0084 0.0073 0.0014 0.0063 0.0074 0.0078 0.0015 0.0081 0.0076 7 0.0355 0.0026 8 0.0373 0.0377 0.0365 0.0012 0.0361 0.036 0.0358 0.0003 0.0369 0.0343 0.0234 0.0238 0.0225 0.0016 9 0.0227 0.0238 0.0241 0.0014 0.024 0.0232 8,000.0 0.0241 0.0168 0.0147 0.0168 0.0021 0.0155 0.0162 0.0157 0.0007 10 0.0157 0.0163 0.0154 0.0009 11 0 0 0 0 0 0 12 0 0 0 13 14 0 0 0 15 0 0 0 0.335 0.022 0.335 0.337 0.018 0.340 0.337 0.330 0.017 Totals 0.343 0.337 0.333 N 10 Ν 10 N 10 Trials 2 3 Oper. 0.335 T1 0.343 T1 T1 0.340 T2 0.337 T2 0.333 T2 0.337 ТЗ 0.335 Т3 0.337 ТЗ 0.330 SUM 1.015 SUM 1.006 SUM 1.007 0.034 Xav 0.034 Xav 0.034 Xav 0.002 0.002 Rav 0.002 Rav Rav 0.034 Raverage 0.002 d₂ 1.128 Xmax **UCLrange** 0.006 D2s 1.910 Xmin 0.034 0.000 D4 3.267 Xdelta 0.000 0.010 Repeatability: Variation in measurement when one operator uses the same instrument and measures the same parts

 Repeatability :
 0.010

 Reproducability :
 0.000

 R&R :
 0.010

 R&R %
 2.78

Variation in measurement due to different operators or instruments, measuring the same parts

Total variation due to repeatability and reproducibility

Measurement System analysis Data Sheet IVS Date: 25-Feb-04 Performed by : Soluris Measurement System CECFN\140\OVERLAY Y direction Measurement Program : USL: 0.15 Operation number : 3534 LSL: -0.15 С operator В T3 R R T2 R T2 Sample T2 ТЗ T3 T1 -0.0224 -0.0223 0.0005 0.0019 -0.021 -0.0217 0.0007 -0.0219 -0.0199 -0.0216 -0.0197 -0.0216 0.0005 0.002 -0.0133 -0.0135 -0.0121 -0.0126 -0.0135 0.0014 -0.0136 -0.014-0.012-0.0138 -0.0175 0.0013 3 -0.015 -0.0164 -0.0169 0.0019 -0.0174 -0.0157 -0.0167 0.0017 -0.0162 -0.017 0.0006 -0.0341 -0.0339 4 -0.0345 -0.0342 -0.03430.0003 -0.0332-0.0347-0.03340.0015 -0.0345-0.0339 -0.033 0.0011 5 -0.0327 -0.0326 -0.0335 0.0009 -0.034-0.0325-0.0336 0.0015 -0.0328 0.0002 0.0006 -0.0257 -0.0255 6 -0.0248 -0.0249 -0.02491E-04 -0.0258-0.0261 -0.0255 -0.02550.0004 0.0016 0.0002 -0.0169 -0.0165 7 -0.0149 -0.0159 -0.0165 -0.0163 -0.0164 -0.0165 -0.0165 0.0007 0.0002 -0.0072 0.0003 -0.0075 -0.0082 8 -0.0067 -0.0069 -0.0069 -0.0075 -0.0072-0.008 0.0007 0.0012 0.0012 -0.0173 -0.018-0.01779 -0.017 -0.0158 -0.0164 -0.0174 -0.0163-0.0175-0.0311 -0.0316 0.0005 -0.0295 -0.0313 -0.0309 0.0018 10 -0.0307 1E-04 -0.0315 -0.0307 -0.0308 0 0 0 11 0 0 0 12 0 0 0 13 0 0 0 14 15 0 0 0 0.010 -0.218 -0.215 -0.216 0.010 -0.216 -0.221 -0.219 0.008 Totals -0.208 -0.212 -0.213 N 10 Ν 10 Ν 10 Trials 2 Oper. 3 Т1 -0.208 T1 -0.218 T1 -0.216 T2 -0.212 T2 -0.215 T2 -0.221 -0.216 ТЗ -0.219 Т3 -0.213 **T3** SUM SUM -0.649 SUM -0.655 -0.633 -0.021 -0.022 -0.022 Xav Xav Xav 0.001 Rav 0.001 Rav 0.001 Rav 1.128 -0.021 Raverage 0.001 d_2 **Xmax** D2s 1.910 -0.022 UCLrange 0.003 Xmin 0.000 D4 3.267 Xdelta 0.001 0.005 Repeatability: Variation in measurement when one operator uses the same instrument and measures the same parts 0.002 Reproducability: Variation in measurement due to different operators or instruments, measuring the same parts R&R: 0.005 Total variation due to repeatability and reproducibility

R&R % :

1.76

Measurement System analysis Data Sheet Measurement System: IVS Date: 25-Feb-04 Performed by : Soluris CECFN\140\OVERLAY X direction Measurement Program: 0.15 3534 LSL: -0.15 USL: Operation number : В С operator Α T1 T2 ТЗ R T2 ТЗ R Sample T1 T2 T3 R T1 0.0878 0.0869 0.0013 0.087 0.0879 0.0872 0.0009 0.0872 0.0866 0.0869 0.0006 0.0882 0.1073 0.1073 0.1081 0.0009 0.1072 0.1073 0.1076 0.0004 2 0.1071 0.1076 0.0005 0.1072 0.0722 0.0724 0.0007 0.0727 0.0728 0.072 0.0008 3 0.0722 0.0716 0.0724 0.0008 0.0729 0.0704 0.0004 0.0693 0.0687 0.0006 4 0.0691 0.0695 0.0695 0.0004 0.0704 0.07 0.0692 0.0907 0.0916 0.0013 0.0892 0.0917 0.0025 5 0.0915 0.0897 0.091 0.0018 0.0903 0.0905 0.0858 0.0849 0.0015 0.0856 0.0862 0.0862 0.0006 6 0.0859 0.0856 0.0858 0.0003 0.0864 0.1262 0.1263 0.1247 0.1258 0.0016 0.1246 0.1254 0.1249 0.0008 7 0.1253 0.1258 0.0009 8 0.0888 0.0892 0.0004 0.0892 0.0886 0.0892 0.0006 0.0887 0.0888 0.0897 0.001 0.089 9 0.0628 0.0632 0.0635 0.0007 0.0636 0.0628 0.0632 0.0008 0.0623 0.0642 0.0625 0.0019 10 0.0592 0.0589 0.0594 0.0005 0.0591 0.0595 0.0597 0.0006 0.0593 0.0593 0.0599 0.0006 11 0 0 0 12 0 0 0 13 0 0 0 14 0 0 0 15 0 0 0 0.850 0.849 0.851 800.0 0.852 0.850 0.853 0.009 0.847 0.849 0.850 0.010 Totals Ν 10 N 10 Ν 10 Trials 2 Oper. 3 T1 0.850 T1 0.852 T1 0.847 T2 0.849 T2 0.850 T2 0.849 Т3 0.851 Т3 0.853 Т3 0.850 SUM 2.550 SUM 2.554 SUM 2.547 Xav 0.085 Xav 0.085 Xav 0.085 Rav 0.001 Rav 0.001 Rav 0.001 Raverage 0.001 d_2 1.128 **Xmax** 0.085 **UCLrange** 0.003 D2s 1.910 0.085 Xmin 0.000 D4 3.267 Xdelta 0.000 Variation in measurement when one operator uses the same instrument and measures the same parts Variation in measurement due to different operators or instruments, measuring the same parts

Repeatability:	0.005
Reproducability:	0.000
R&R :	0.005
R&R % :	1.58

Total variation due to repeatability and reproducibility

Measurement System analysis Data Sheet Measurement System: IVS Date: 25-Feb-04 Performed by: Soluris CECFN\090\OVERLAY Y direction Measurement Program: 3527 LSL: -0.1 USL: 0.1 Operation number : С R operator T2 R T3 R T2 ТЗ R T1 ТЗ Sample T1 T2 T1 -0.0204 -0.021 0.001 -0.0216 -0.0213 -0.0205 0.0011 -0.0223 -0.02 -0.0207 0.0023 -0.0214 0.0006 8000.0 -0.0136 -0.0116 -0.0115 0.0021 2 -0.013-0.0124 -0.0128 -0.0121 -0.0129 -0.01270.0023 0.0082 0.0011 0.0074 0.0082 0.0012 3 0.0091 0.0081 0.0068 0.0079 0.009 0.0086 0.0006 0.0043 0.0004 4 0.0037 0.0039 0.005 0.0013 0.0051 0.0045 0.0048 0.0046 0.0042 -0.0258 -0.0289 0.0031 -0.0255 0.002 5 -0.0253 -0.0255 -0.0249 0.0006 -0.0263 -0.0262 -0.02750.0007 -0.0021 0.0017 -0.0018 -0.0011 6 -0.0028 -0.0007 -0.0008 0.0021 -0.0006 -0.0023-0.0011 7 0.0014 -0.0398 0.0015 -0.0409 -0.0406-0.0406 -0.0399 -0.0424 0.0025 -0.0407-0.0413-0.0420.0019 8 -0.0284 0.0011 -0.0281 -0.0289 -0.0278 0.0011 -0.0299 -0.0283 -0.028 -0.029-0.0279 0.0009 9 -0.0105 0.0031 -0.0082 -0.008 -0.0086 0.0006 -0.0085 -0.0094-0.0085 -0.0111-0.008 10 -0.0095 0.0006 -0.0105 -0.01 -0.0092 0.0013 -0.0106 -0.0088 -0.0107 0.0019 -0.0097 -0.0101 0 0 11 0 12 0 0 0 13 0 0 0 14 0 0 0 15 0 0 0 -0.138 -0.134 -0.139 0.015 -0.134 -0.136 0.013 -0.141 -0.135 -0.136 0.015 Totals -0.139 Ν Ν 10 Ν 10 10 Trials 2 Oper. 3 T1 -0.139 T1 -0.134 T1 -0.141 T2 -0.134 T2 -0.136 T2 -0.135 ТЗ -0.138 Т3 -0.136 Т3 -0.139 SUM -0.412 SUM -0.409 SUM -0.412 -0.014 -0.014 Xav -0.014 Xav Xav Rav 0.002 Rav 0.001 Rav 0.001 Raverage 0.001 1.128 -0.014 d_2 **Xmax** UCLrange 0.005 D2s 1.910 -0.014 Xmin 0.000 D4 3.267 Xdelta 0.000 0.008 Repeatability: Variation in measurement when one operator uses the same instrument and measures the same parts Reproducability: 0.000 Variation in measurement due to different operators or instruments, measuring the same parts R&R: 0.008 Total variation due to repeatability and reproducibility

Percent of the tolerance that is taken up by measurement error

R&R %:

3.80

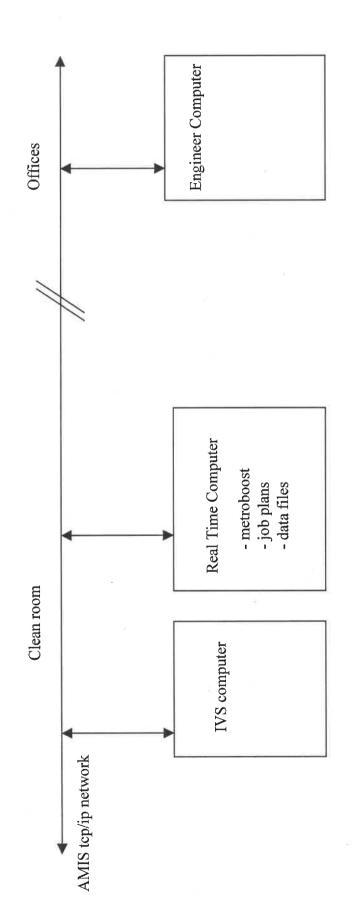
Measurement System analysis Data Sheet Performed by : Soluris Measurement System: IVS Date: 25-Feb-04 CECFN\090\OVERLAY X direction Measurement Program: 3527 LSL: -0.1 USL: 0.1 Operation number : R С operator T3 R T2 T3 R T1 T2 Т3 R T2 T1 Sample T1 -0.05 0.0021 -0.0501 -0.0502 -0.0491 0.0011 -0.0497 -0.0494 -0.0498 0.0004 -0.0479 -0.0499 0.0016 0.0396 0.0392 0.0015 0.0413 0.0012 0.0407 0.0414 0.0398 0.0407 0.0401 0.0407 -0.0533 0.0026 -0.0507 -0.0508 0.0004 -0.05 0.0005 -0.0529 -0.0507-0.0511 3 -0.0504 -0.04990.0012 0.0527 0.0531 0.0011 0.0524 0.0005 0.0531 0.0519 0.053 0.052 4 0.0525 0.0529 -0.0568 0.002 -0.0557 -0.0577 0.002 5 -0.0548 0.001 -0.0551 -0.0548-0.0557-0.0558 -0.0555 0.0012 0.0702 0.07 0.0005 0.0695 0.0002 0.0685 0.069 0.0697 0.0697 6 0.0694 0.0693 7 -0.0281 0.0015 -0.0288 -0.0295 -0.0294 0.0007 -0.0281 0.0008 -0.0286 -0.0296-0.0287 -0.02890.0016 0.0617 0.0624 0.0007 0.0618 0.0628 0.0624 0.001 8 0.0611 0.0627 0.0617 0.0619 0.0011 -0.0205 -0.0208 -0.0211 0.0006 -0.0207 -0.0197 -0.0205 0.001 9 -0.0197 -0.0208 -0.0208 10 0.0708 0.0714 0.0022 0.0732 0.0727 0.0719 0.0013 0.0721 0.0726 0.0733 0.0012 0.073 11 0 0 0 0 12 0 0 0 13 0 0 0 14 0 0 0 15 0 0 0.090 Totals 0.094 0.091 0.093 0.011 0.090 0.088 0.092 0.014 0.090 0.093 0.010 10 Ν 10 10 Ν Oper. Trials 2 3 0.090 T1 0.094 T1 0.090 T1 T2 0.091 T2 0.088 T2 0.093 ТЗ 0.093 ТЗ 0.092 Т3 0.090 SUM 0.278 SUM 0.269 SUM 0.273 Xav 0.009 Xav 0.009 Xav 0.009 Rav 0.001 Rav 0.001 Rav 0.001 1.128 0.009 Raverage 0.001 d_2 Xmax UCLrange 0.004 D2s 1.910 Xmin 0.009 0.000 0.000 D4 3.267 Xdelta 0.006 Repeatability: Variation in measurement when one operator uses the same instrument and measures the same parts Reproducability: 0.000 Variation in measurement due to different operators or instruments, measuring the same parts Total variation due to repeatability and reproducibility

R&R: 0.006

3.09

R&R %:

IVS 130 Networking configuration



- IVS computer will send data file to real time computer to get Overlay Booster analysis

- IVS job plans and data files can be stored on real time computer: from the office you can open, analyze data files from engineer computer



IVS 130

Factory Qualification Test

Prepared For:

Leo Schlegel

Sr. Process Engineer

AMI Semiconductor Belgium BVBA

Tel: +32 55 332 464

Fax: +32 55 332 223

leo_schlegel@amis.com

Prepared By:

John Podlesny

Applications Group Leader

Soluris Inc.

Tel: (978)815-5904

Fax: (480)897-0503

JPodlesny@soluris.com

Revision 1.0

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I. Wafer Handling

The IVS 130 will transfer 1500 monitor wafers in a dynamic mode including: transferring wafers to the pre-aligner; finding the flat/notch; transferring the wafers to the stage; and replacing the wafers in the cassette. This test shall be performed allowing for no more than one failure. A failure will result with a handler system error code in the printed data. This test will be divided into three sessions with 500 wafers per cassette platform $(3 \times 500 = 1500 \text{ total wafers})$.

CASSETTE PLATFORM	WAFERS CYCLED	LOAD ANGLE MIN	LOAD ANGLE MAX	LOAD ANGLE RANGE	NUMBER OF FAILURES	SPEC. (percent)
Α	500	0.0450	0.2500	0.2050	0	99.0
В	500	-0.0410	0.2030	0.2440	0	99.0
С	500	-0.0640	0.1350	0.1990	0	99.0

II. Metrology

A. Overlay Registration Test – Precision

The precision of the system overlay registration performance shall be demonstrated on four standard production layers as described below. This test will be performed using optimized job plans. These wafers will be selected from Customer standard production lots. One mutually acceptable wafer shall be provided for each of the registration test layers.

Test Procedure: This test shall include measuring box-in-box, box-in-frame, or bar-in-bar overlay registration marks on 5 fields, 2 sites per field, at agreed to locations across the wafers described. It is assumed the targets will be equivalent to IVS' standard specification for box-in-box feature dimensions which are: 10 microns for the inner box and 20 microns for the outer box. As a general rule, the inner edge of the outer box should have a dimension which is twice that of the inner box dimension. Ten dynamic mode measurements (wafer load/unload between measurements) for each site shall be taken.

Specification: Pooled 3 Sigma Standard Deviation \leq 2.5 nanometers for each wafer. Worst Case 3 Sigma Standard Deviation \leq 6.0 nanometers for any given site. It should be noted that system performance may be affected by: extremely grainy films, targets distorted by CMP, film thickness variations and edge slope variations more than +/-10% in the targeted measurement area

SLOT	WAFER ID	X POOLED 3g in nm	Y POOLED 3 ₀ in nm	SPEC. 3ø in nm
1	APSC N/10vs5/rg			2.5
3	HIMQ N/180vs160/rg			2.5
5	CECF_N/90vs60/rg			2.5
7	CECF_N/140vs130/rg			2.5 .

B. Overlay Registration Test – Tool Induced Shift:

The system Tool Induced Shift (TIS) performance shall be demonstrated on the wafers from Section II.A.

Test Procedure: This test shall include measuring ten box-in-box overlay registration marks at agreed to locations across the wafer described. Ten static mode measurements for each site shall be taken. This test shall be run after IVS has performed the RG180 calibration process. TIS shall be calculated as follows: ((reg. measurement means for x, y axes with the notch or flat at 0 degrees) + (reg. measurement means for x, y axes with the **notch or** flat at 180 degrees))/2.

Specification: Mean Value of TIS (for both x and y axis) ≤ ±2 nanometers

Worst Case Value of TIS (for both x and y axis) $\leq \pm 5$ nanometers

It should be noted that system performance may be affected by: extremely grainy films, targets distorted by CMP, film thickness variations and edge slope variations more than +/-10% in the targeted measurement area.

SLOT	WAFER ID	X AXIS TIS Average In nm	Y AXIS TIS Average In nm	SPEC. In nm
1	APSC_N/10vs5/rg	-		±2.00
3	HIMQ_N/180vs160/rg			±2.00
5	CECF_N/60vs90/rg			±2.00
7	CECF_N/140vs130/rg			±2.00

C. Critical Dimension Test - Precision

The precision of the system CD performance shall be demonstrated on four standard production layers as described below. One mutually acceptable wafer shall be provided for each of the four CD test layers defined. This specification addresses the 100x lens. Specifications for measurements using the 5x, 20x, 50, and 150x lenses will be quoted upon request.

Test Procedure: This test shall include measuring an agreed to nominal greater than or equal to 1.0 micron line at five CD sites across the wafers described. Ten dynamic mode measurements (wafer load/unload between measurements) for each site shall be taken.

Specification: Pooled 3 Sigma Standard Deviation ≤12 nanometers, or 1%, whichever is greater.

SLOT	WAFER ID	POOLED 3σ in nm	SPEC. 3 ₀ in nm
19	J454_O/125/CD	4.87	13.9
21	CORA_O/160M/CD	2.18	12.0
23	AGDA_N/9/CD	11.20	12.0
25	CORA_O/160R/CD	9.29	14.4

D. Pitch - Accuracy and Precision

The accuracy and precision of the tool shall be demonstrated on at least 1 VLSI wafer. Pitch measurements shall be made on 2 and 4 um targets.

Test Procedure: This test shall include measuring a VLSI certified pitch standard. The 2.0 and 4.0 um pitch targets shall be measured ten times dynamically, and their mean and precision values shall be taken.

SLOT	WAFER ID	PITCH in um	POOLED 3σ in nm
16	LWS-2620 2um	1.996	2.4
16	LWS-2620 4 um	3.981	3.3
25	LWS-2620 2um	1.985	1.5
25	LWS-2620 4 um	3.987	2.7
19	LWS-2620 2um	1.992	3.0
19	LWS-2620 4 um	3.981	3.0

III. Focus and Pattern Recognition:

The IVS 130 shall be able to focus and perform the pattern recognition function successfully 98% of the time on the production wafer layers defined in Section II.A and II.C. If a failure occurs, the system must continue to process wafers unassisted. A failure will result with a focus or pattern recognition system error code in the data. No wafers with known pattern defects shall be used in the testing.

SLOT	WAFER ID	NUMBER OF SITE LOCATES	PATTERN RECOGNITION (percent)	SPEC. (percent)
1	APSC_N/10vs5/rg	10		98.0
3	HIMQ_N/180vs160/rg	10		98.0
5	CECF_N/60vs90/rg	10		98.0
7	CECF_N/140vs130/rg	10		98.0
19	J454_O/125/CD	5	100.0	98.0
21	CORA_O/160M/CD	5	100.0	98.0
23	AGDA_N/9/CD	5	100.0	98.0
25	CORA_O/160R/CD	5	100.0	98.0

IV. System Throughput Test:

A. Throughput Test - 5 die/wafer; 1 site/die:

System throughput shall include measuring one registration feature in the x and y axes at each of five sites per wafer. The test will measure one layer type and will use a single job. IVS' Edge Focus method along with the grey scale pattern recognition method shall be used. System throughput shall be measured starting at the beginning of the vacuum sensing of the first wafer on the stage and ending with the tenth wafer from the stage at vacuum sense off. In the event that 10 wafers are not provided, one wafer shall be measured 10 times, and throughput shall be measured starting at the beginning of the vacuum sensing of the wafer on the stage and ending when the wafer is taken from the stage and the vacuum sensing turns off.

Specification: The system shall measure 90 wafers per hour performed on ten wafers using one of the standard production layers identified in section II.A.

RUN	WAFER ID	Wafer Time In Sec.	Throughput In WPH	SPEC. In WPH
1		40	90.0	
2		39	92.3	
3		40	90.0	
4		40	90.0	
5		39	92.3	
6		41	87.8	
7		39	92.3	
8		41	87.8	
9		40	90.0	
10		40	90.0	
Average:			90.3	90

V. Particle Count:

The IVS 130 shall not add more than 10 particles, per pass per eight inch wafer, 0.1 microns in size or larger. Five test wafers and five control wafers shall be measured for particulates before the test. The test wafers shall: transfer from the cassette to the flat finder; transfer the wafer to the stage; rotate objectives; and then be replaced in the cassette. The control wafers shall be set on top of the IVS 130 to establish a background particulate level. This procedure shall be repeated five times for each wafer. The test and control wafers shall be particulate tested after completion of the ten passes. The environment around the system shall be isolated and/or be controlled for this test.

Particles per wafer, per pass, shall defined as:

 $PWP = W \times n \times (PG_{test} - PG_{control})$

PWP = Particles per Wafer per Pass

W = Number of wafers measured

n = Number of passes through the system

PG = (Particles measured after the test) - (Particles measured before the test)

It is expected that the particle test will be run within a reasonable period of time in comparison to when the rest of the system acceptance tests are run.

SLOT	WAFER ID	CHANGE CONTROL WAFERS	AVERAGE PARTICLE COUNT	SPEC. (Particles
1	Sample			≤10.0
2	Control			
3	Sample			≤10.0
4	Control			
5	Sample			≤10.0
6	Control			
7	Sample			≤10.0
8	Control			
9	Sample		·	≤10.0
10	Control			

To be performed at installation only

VI. Software

The system software will operate according to the description in the User's Manual. Any software releases will be accompanied by a set of Release Notes which will detail the changes to the system software and operations. This documentation will be provided in a format similar to the User's Manual which will allow for the material to be added as an addendum to the manual.

In the event the optional GEM communications package is purchased, the package shall function as described in the SEMI E30-94 document excluding the limits monitoring capability. Soluris will quote modifications to this package upon request.

In the event the optional SECS II communications package is purchased, the package shall function in accordance with Soluris' specifications.

In the event the Metroboost Overlay Booster Stepper Optimization Package is purchased, the package shall provide the functionality associated with v2.38 and higher, and will be in accordance with the Overlay Booster User Guide. Soluris will quote additions and modifications to this package upon request.

In the event the optional Monolith Stepper Analysis package is purchased with real-time capability, the package shall function in accordance with the NVS Monolith manual. Soluris will quote additions and modifications to this package upon request.

VII. Miscellaneous:

The above acceptance test specification is subject to Soluris' pre-examination of the wafers that will be used for this test. It should be noted that system performance may be affected by: extremely grainy films, film thickness variations and edge slope variations more than +/-10% in the targeted measurement area. After Soluris has reviewed the wafers submitted for the Acceptance Test, a final commitment will be made concerning the actual system performance specifications.

The system shall be considered accepted by **AMIS**, and warranty shall begin: 1. After successful completion of the agreed-to acceptance test, and sign-off by **AMIS** OR upon beneficial use by **AMIS** Beneficial use is defined as using the system for something other than testing, including but not limited to pilot production, engineering test lots, production, and device prototyping. In cases where the facility and/or utilities are not ready as committed by customer, customer is liable for revisit expenses.

The equipment shall be available and fully operational 95% of the time. A call reporting that the equipment is down must be made to Soluris before system down time can begin. Soluris Customer Service provides on-site technical support during normal business hours, which are Monday through Friday, 8:30 am to 5:30 PM local time (exclusive of Soluris Holidays) during the Warranty period. Soluris also provides Answering Service support 7 days per week, 24 hours per day. This service will route your incoming calls accordingly. Wafers for the above tests shall be provided to Soluris as soon as possible although no later than six weeks prior to the scheduled shipment date. These wafers shall be used for the factory acceptance and the final acceptance testing at the customer facility.

VIII. System Facory Acceptance Testing

The IVS 130 has successfully demonstrated the capability expected by the customer for Source Acceptance. Shipment from Soluris is authorized.

John Podlesny	Date
Applications Group Leader	
Soluris Inc.	
·	
Leo Schlegel	Date
Sr. Process Engineer	
AMI Semiconductor Belgium BVBA	N/



IVS 130

On site Qualification Test

Prepared For:

Leo Schlegel

Sr. Process Engineer

AMI Semiconductor Belgium BVBA

Tel: +32 55 332 464 Fax: +32 55 332 223

leo_schlegel@amis.com

Prepared By:

Marc Poulingue

Applications Engineer

Soluris Inc.

Tel: +33 (0)6 20 17 15 69

Fax: + 1 978 287 0138

mpoulingue@soluris.com

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I. Wafer Handling

The IVS 130 will transfer 1500 monitor wafers in a dynamic mode including: transferring wafers to the pre-aligner; finding the flat/notch; transferring the wafers to the stage; and replacing the wafers in the cassette. This test shall be performed allowing for no more than one failure. A failure will result with a handler system error code in the printed data. This test will be divided into three sessions with 500 wafers per cassette platform ($3 \times 500 = 1500$ total wafers).

CASSETTE PLATFORM	WAFERS CYCLED	LOAD ANGLE MIN	LOAD ANGLE MAX	LOAD ANGLE RANGE	NUMBER OF FAILURES	SPEC. (percent)
A +	500	0.1090	0.2740	0.1650	0	99.0
В	500	0.0510	0.2260	0.1750	0	99.0
С	500	0.0500	0.2210	0.1710	0	99.0

II. Metrology

A. Overlay Registration Test – Precision

The precision of the system overlay registration performance shall be demonstrated on four standard production layers as described below. This test will be performed using optimized job plans. These wafers will be selected from Customer standard production lots. One mutually acceptable wafer shall be provided for each of the registration test layers.

Test Procedure: This test shall include measuring box-in-box, box-in-frame, or bar-in-bar overlay registration marks on 5 fields, 2 sites per field, at agreed to locations across the wafers described. It is assumed the targets will be equivalent to IVS' standard specification for box-in-box feature dimensions which are: 10 microns for the inner box and 20 microns for the outer box. As a general rule, the inner edge of the outer box should have a dimension which is twice that of the inner box dimension. Ten dynamic mode measurements (wafer load/unload between measurements) for each site shall be taken.

Specification: Pooled 3 Sigma Standard Deviation \leq 2.5 nanometers for each wafer. Worst Case 3 Sigma Standard Deviation \leq 6.0 nanometers for any given site. It should be noted that system performance may be affected by: extremely grainy films, targets distorted by CMP, film thickness variations and edge slope variations more than +/-10% in the targeted measurement area

SLOT	WAFER ID	X – POOLED 3 ₀ in nm	Y – POOLED 3 _o in nm	SPEC. 3 _o in nm
1	APSC N/10vs5/rg	1.9	3.2	4.0
3	HIMQ N/180vs160/rg	3.1	5.3	6.0
5	CECF_N/90vs60/rg	2.0	2.3	2.5
7	CECF_N/140vs130/rg	1.6	1.9	2.5

B. Overlay Registration Test – Tool Induced Shift:

The system Tool Induced Shift (TIS) performance shall be demonstrated on the wafers from Section II.A.

Test Procedure: This test shall include measuring ten box-in-box overlay registration marks at agreed to locations across the wafer described. Ten static mode measurements for each site shall be taken. This test shall be run after IVS has performed the RG180 calibration process. TIS shall be calculated as follows: ((reg. measurement means for x, y axes with the notch or flat at 0 degrees) + (reg. measurement means for x, y axes with the **notch or** flat at 180 degrees))/2.

Specification: Mean Value of TIS (for both x and y axis) $\leq \pm 2$ nanometers Worst Case Value of TIS (for both x and y axis) $\leq \pm 5$ nanometers

It should be noted that system performance may be affected by: extremely grainy films, targets distorted by CMP, film thickness variations and edge slope variations more than +/-10% in the targeted measurement area.

SLOT	WAFER ID	X AXIS TIS Average In nm	Y AXIS TIS Average In nm	SPEC. In nm
1	APSC_N/10vs5/rg	0.2	0.3	±2.00
3	HIMQ_N/180vs160/rg	-0.9	0.2	±2.00
5	CECF_N/60vs90/rg	0.2	0.2	±2.00
7	CECF_N/140vs130/rg	0.6	0.7	±2.00

C. Critical Dimension Test - Precision

The precision of the system CD performance shall be demonstrated on four standard production layers as described below. One mutually acceptable wafer shall be provided for each of the four CD test layers defined. This specification addresses the 100x lens. Specifications for measurements using the 5x, 20x, 50, and 150x lenses will be quoted upon request.

Test Procedure: This test shall include measuring an agreed to nominal greater than or equal to 1.0 micron line at five CD sites across the wafers described. Ten dynamic mode measurements (wafer load/unload between measurements) for each site shall be taken.

Specification: Pooled 3 Sigma Standard Deviation ≤12 nanometers, or 1%, whichever is greater.

SLOT	WAFER ID	POOLED 3σ in nm	SPEC. 3 _o in nm
19	J454_O/125/CD	5.0	13.9
21	CORA_O/160M/CD	1.9	12.0
23	AGDA_N/9/CD	11.8	12.0
25	CORA O/160R/CD	8.4	14.3

D. Pitch - Accuracy and Precision

The accuracy and precision of the tool shall be demonstrated on at least 1 VLSI wafer. Pitch measurements shall be made on 2 and 4 um targets.

Test Procedure: This test shall include measuring a VLSI certified pitch standard. The 2.0 and 4.0 um pitch targets shall be measured ten times dynamically, and their mean and precision values shall be taken.

SLOT	WAFER ID	PITCH in um	POOLED 3 _o in nm
16	LWS-2640 2um	2.0011	2.5
16	LWS-2640 4 um	3.9989	4.2

III. Focus and Pattern Recognition:

The IVS 130 shall be able to focus and perform the pattern recognition function successfully 98% of the time on the production wafer layers defined in Section II.A and II.C. If a failure occurs, the system must continue to process wafers unassisted. A failure will result with a focus or pattern recognition system error code in the data. No wafers with known pattern defects shall be used in the testing.

SLOT	WAFER ID	NUMBER OF SITE LOCATES	PATTERN RECOGNITION (percent)	SPEC. (percent)
1	APSC_N/10vs5/rg	10	100.0	98.0
3	HIMQ_N/180vs160/rg	10	100.0	98.0
5	CECF_N/60vs90/rg	10	100.0	98.0
7	CECF_N/140vs130/rg	10	100.0	98.0
19	J454_O/125/CD	5	100.0	98.0
21	CORA O/160M/CD	5	100.0	98.0
23	AGDA N/9/CD	5	100.0	98.0
25	CORA_O/160R/CD	5	100.0	98.0

IV. System Throughput Test:

A. Throughput Test - 5 die/wafer; 1 site/die:

System throughput shall include measuring one registration feature in the x and y axes Page 5 of 9

at each of five sites per wafer. The test will measure one layer type and will use a single job. IVS' Edge Focus method along with the grey scale pattern recognition method shall be used. System throughput shall be measured starting at the beginning of the vacuum sensing of the first wafer on the stage and ending with the tenth wafer from the stage at vacuum sense off. In the event that 10 wafers are not provided, one wafer shall be measured 10 times, and throughput shall be measured starting at the beginning of the vacuum sensing of the wafer on the stage and ending when the wafer is taken from the stage and the vacuum sensing turns off.

Specification: The system shall measure 90 wafers per hour performed on ten wafers using one of the standard production layers identified in section II.A.

RUN	WAFER ID	Wafer Time In Sec.	Throughput In WPH	SPEC. In WPH
1		39	92.3	
2		40	90.0	
3		39	92.3	
4		38	94.7	
5		40	90.0	
6		39	92.3	
7		41	87.8	
8		40	90.0	
9		40	90.0	
10		40	90.0	
verage:			90.9	90

V. Particle Count:

The IVS 130 shall not add more than 10 particles, per pass per eight inch wafer, 0.1 microns in size or larger. Five test wafers and five control wafers shall be measured for particulates before the test. The test wafers shall: transfer from the cassette to the flat finder; transfer the wafer to the stage; rotate objectives; and then be replaced in the cassette. The control wafers shall be set on top of the IVS 130 to establish a background particulate level. This procedure shall be repeated five times for each wafer. The test and control wafers shall be particulate tested after completion of the ten passes. The environment around the system shall be isolated and/or be controlled for this test.

Particles per wafer, per pass, shall defined as:

PWP = $W \times n \times (PG_{test} - PG_{control}) = 5x5x-2=-50$

PWP = Particles per Wafer per Pass

W = Number of wafers measured

n = Number of passes through the system

PG = (Particles measured after the test) - (Particles measured before the test)

It is expected that the particle test will be run within a reasonable period of time in comparison to when the rest of the system acceptance tests are run.

SLOT	WAFER ID	PARTICL E BEFORE TEST	PARTICL E AFTER TEST	Delta	SPEC. (Particles
1	Sample	1	1	0	≤10.0
2	Control	6	7	1	
3	Sample	0	0	0	≤10.0
4	Control	12	12	0	
5	Sample	2	2	0	≤10.0
6	Control	3	4	1	
7	Sample	1	1	0	≤10.0
8	Control	6	8	2	
9	Sample	8	6	-2	≤10.0
10	Control	5	6	1	

VI. Software

The system software will operate according to the description in the User's Manual. Any software releases will be accompanied by a set of Release Notes which will detail the changes to the system software and operations. This documentation will be provided in a format similar to the User's Manual which will allow for the material to be added as an addendum to the manual.

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accordance with the Overlay Booster User Guide. Soluris will quote additions and modifications to this package upon request.

In the event the optional Monolith Stepper Analysis package is purchased with real-time capability, the package shall function in accordance with the NVS Monolith manual. Soluris will quote additions and modifications to this package upon request.

VII. Miscellaneous:

The above acceptance test specification is subject to Soluris' pre-examination of the wafers that will be used for this test. It should be noted that system performance may be affected by: extremely grainy films, film thickness variations and edge slope variations more than +/-10% in the targeted measurement area. After Soluris has reviewed the wafers submitted for the Acceptance Test, a final commitment will be made concerning the actual system performance specifications.

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The equipment shall be available and fully operational 95% of the time. A call reporting that the equipment is down must be made to Soluris before system down time can begin. Soluris Customer Service provides on-site technical support during normal business hours, which are Monday through Friday, 8:30 am to 5:30 PM local time (exclusive of Soluris Holidays) during the Warranty period. Soluris also provides Answering Service support 7 days per week, 24 hours per day. This service will route your incoming calls accordingly. Wafers for the above tests shall be provided to Soluris as soon as possible although no later than six weeks prior to the scheduled shipment date. These wafers shall be used for the factory acceptance and the final acceptance testing at the customer facility.

VIII. System Facory Acceptance Testing

The IVS 130 has successfully demonstrated the capability expected by the customer for Source Acceptance. Shipment from Soluris is authorized.

Marc Poulingue

Feb. 27, 2004 Date

Applications Engineer

Soluris Inc.

Leo Schlegel

Feb. 27, 2004

Date

Sr. Process Engineer AMI Semiconductor Belgium BVBA

Measurement System analysis Data Sheet												
Measurement System : IVS				Date :	25-Feb-04 Performed by :			Soluris				
Measurement Program :			APSCN/010/OVERLAY - Y direction]							
Operation	number :	nwell i2T	LSL:	-0.3	USL:	0.3	1 :					
operator		А				В				С		
Sample	T1	T2	Т3	R	T1	T2	T3	R	T1	T2	T3	R
1	-0.0066	-0.0064		0.0008	-0.0049	-0.0044	-0.0042	0.0007	-0.0062	-0.0072	-0.0065	0.001
2	0.0193	0.0177	0.0176	0.0017	0.0194	0.0204	0.0195	0.001	0.0191	0.0191	0.0177	0.0014
3	-0.0043	-0.0055	-0.0075	0.0032	-0.005	-0.0049	-0.0055	0.0006	-0.0056	-0.0054	-0.0068	0.0014
4	0.0013	-0.0008	-0.0002	0.0021	0.0013	0.0006	-0.0004	0.0017	0.0026	-0.0012	-0.0003	0.0038
5	-0.0032	-0.0035	-0.0057	0.0025	-0.0036	-0.0063	-0.0031	0.0032	-0.0062	-0.0046	-0.005	0.0016
6	-0.0113	-0.0088	-0.0088	0.0025	-0.0091	-0.0068	-0.0085	0.0023	-0.008	-0.0084	-0.0081	0.0004
7	-0.0005	-0.0016	-0.0011	0.0011	-0.0032	-0.0017	-0.0019	0.0015	-0.0026	-0.0015	-0.0005	0.0004
8	0.0148	0.0126	0.0158	0.0032	0.0129	0.0141	0.0139	0.0013	0.015	0.0144	1	
9	0.0211	0.0213	0.0224	0.0013	0.0206	0.0226	0.0234	0.0028	0.013		0.0138	0.0012
10	-0.0014	0.0005	-0.0013	0.0019	-0.0006	-0.0012	-0.0004	0.0028	4	0.0203	0.0225	0.0022
11			0.0010	0.0010	0.0000	-0.0012	-0.0004		-0.0022	-0.0022	0.0009	0.0031
12				0				0				0
13				0				ď				0
14			-					0				0
15				0				0				0
10				0				0				0
Totals	0.029	0.026	0.025	0.020	0.028	0.032	0.033	0.016	0.027	0.023	0.028	0.018
N	10		,	N	10			N	10	7.5		
Trials	2		l	Oper.	3							
4	T1	0.029			T1	0.028			T1	0.007		
1	T2	0.026			T2	0.020				0.027		
1	T3	0.025			T3	0.032			T2	0.023		
1	SUM	0.080			SUM				T3	0.028		
1	Xav	0.003				0.093			SUM	0.078		
1	Rav	0.003		-	Xav	0.003			Xav	0.003		
Į.	Nav	0.002		ı	Rav	0.002			Rav	0.002		
Raverage	0.002		:	[d ₂	1.128	Γ	Xmax	0.003			
UCLrange	0.006				D2s	1.910		Xmin	0.003			
)				[D4	3.267		Xdelta	0.001	0.000		
Repeatabilit	y:	0.010										
		Variation in measurement when one operator uses the same instrument and measures the same parts										
Reproducability: 0.000		Variation in measurement due to different operators or instruments, measuring the same parts										
R&R: 0.010		Total variation due to repeatability and reproducibility										
R&R % : 1.60		Percent of the tolerance that is taken up by measurement error										